

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
03 November 2022 (03.11.2022)



(10) International Publication Number
WO 2022/231760 A1

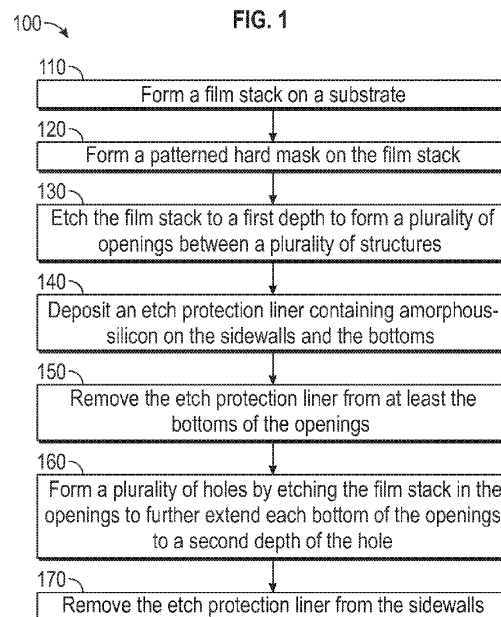
- (51) **International Patent Classification:**
H01L 21/311 (2006.01) *H01L 27/112* (2006.01)
- (21) **International Application Number:**
PCT/US2022/022988
- (22) **International Filing Date:**
01 April 2022 (01.04.2022)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
17/246,209 30 April 2021 (30.04.2021) US
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(81) **Designated States** (*unless otherwise indicated, for every
kind of national protection available*): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO,
DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,
HR, HU, ID, IL, IN, IR, IS, IT, JM, JO, JP, KE, KG, KH,
KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA,
MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI,
NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU,
RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM,

(54) **Title:** PROCESSES TO DEPOSIT AMORPHOUS-SILICON ETCH PROTECTION LINER



(57) **Abstract:** Embodiments of the present disclosure generally relate to fabricating electronic devices, such as memory devices. In one or more embodiments, a method for forming a device includes forming a film stack on a substrate, where the film stack contains a plurality of alternating layers of oxide layers and nitride layers and has a stack thickness, and etching the film stack to a first depth to form a plurality of openings between a plurality of structures. The method includes depositing an etch protection liner containing amorphous-silicon on the sidewalls and the bottoms of the structures, removing the etch protection liner from at least the bottoms of the openings, forming a plurality of holes by etching the film stack in the openings to further extend each bottom of the openings to a second depth of the hole, and removing the etch protection liner from the sidewalls.

[Continued on next page]

TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))